

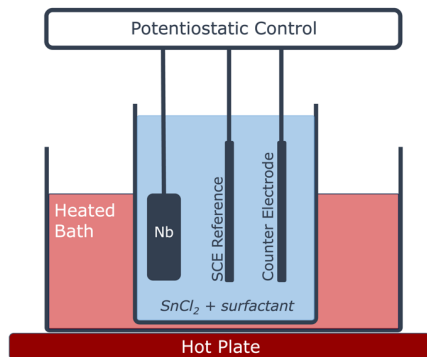
Goal for conduction-cooled SRF cavity technology: Reach higher  $Q_0$  at 4.2K

Main challenge: achieve a smooth Nb<sub>3</sub>Sn film with uniform thickness and stoichiometry

→ Improving vapor diffusion:

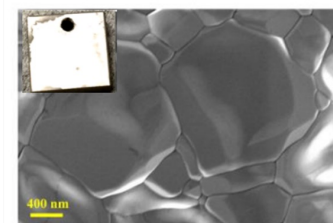
sample studies have shown that pre-nucleation chemical treatments affect tin coverage on Nb substrate

→ Alternative growth method: electrochemical synthesis

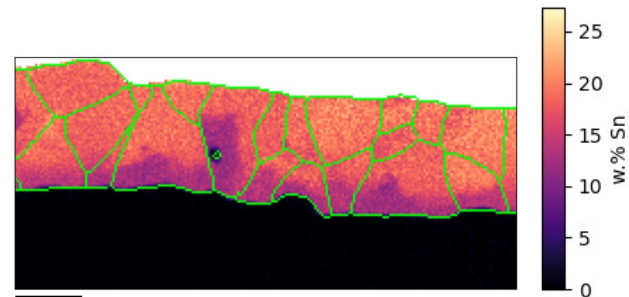


Electrochemical deposition

Anneal > 900°C to thermally convert to stoichiometric, smooth Nb<sub>3</sub>Sn

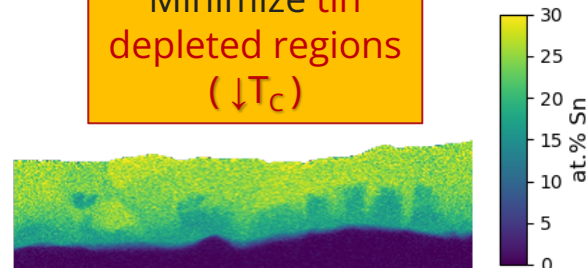


Lower surface roughness



1 μm

Minimize tin depleted regions (↓T<sub>c</sub>)

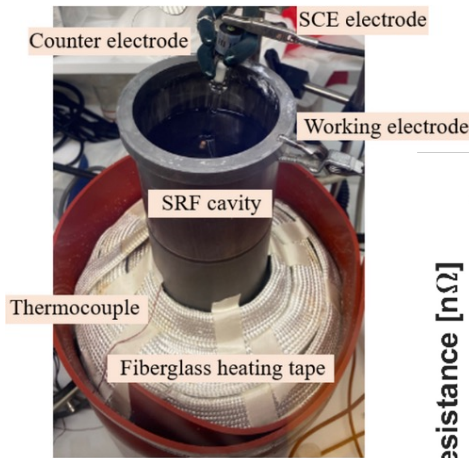
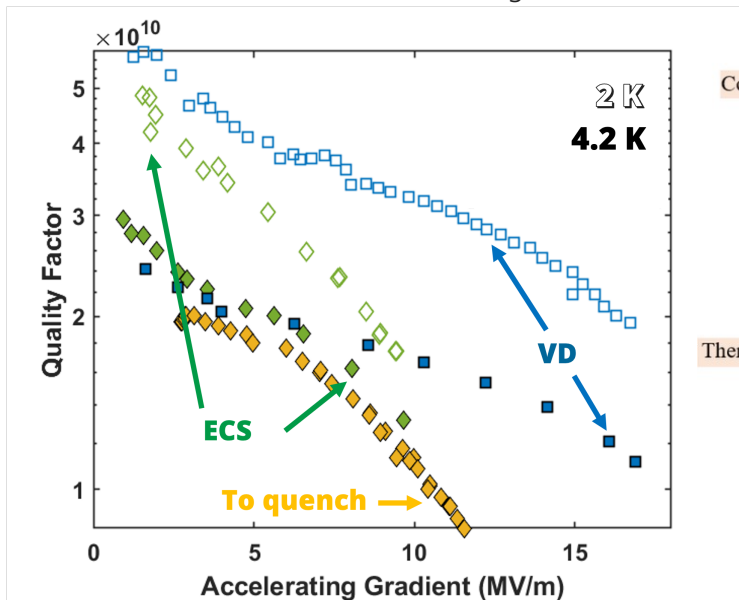


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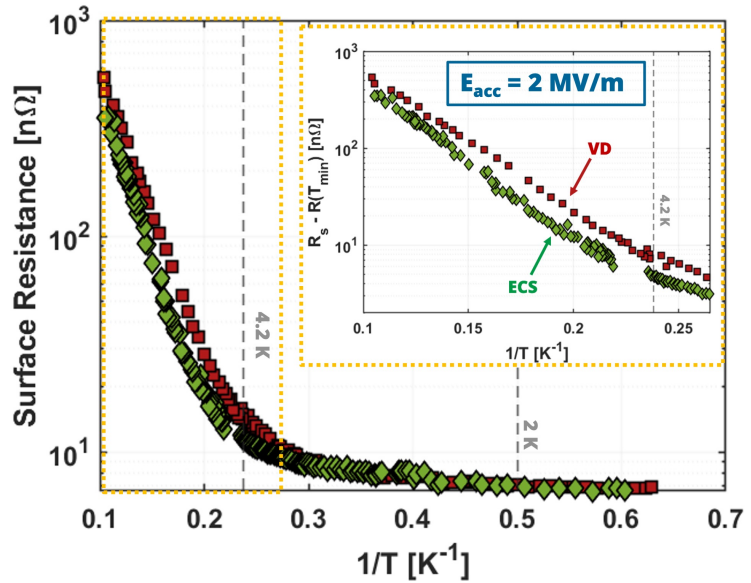
# Proof of Principle: Electrochemical Synthesis

This alternative growth method provides **uniform tin nucleation** and **sufficient Sn supply** in critical times

⇒ **smoother** Nb<sub>3</sub>Sn films with **little variation in Sn concentration with depth**.



→ Very low BCS low resistance



→ First ever alternative growth method to vapor diffusion to achieve **quality factors  $>10^{10}$**  at **4.2 K**